

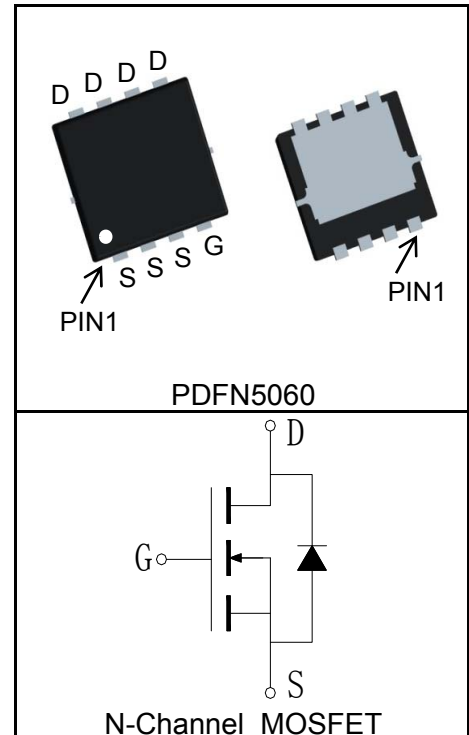
Features

- 30V/90A,
- $R_{DS(ON)} = 2.8m\Omega(Typ.)@V_{GS}=10V$
- $R_{DS(ON)} = 3.4m\Omega(Typ.)@V_{GS}=4.5V$
- Super High Dense Cell Design
- Ultra Low On-Resistance
- Fast Switching Speed
- 100% avalanche tested
- Lead Free and Green Devices Available (RoHS Compliant)

Applications

- DC/DC Converters
- Load switch
- Synchronous rectification

Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _C =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	T _C =25°C	50	A
Mounted on Large Heat Sink				
I _{DP} ^①	300μs Pulse Drain Current Tested	T _C =25°C	360	A
I _D ^②	Continuous Drain Current@T _C (V _{GS} =10V)	T _C =25°C	90	A
		T _C =100°C	57	
	Continuous Drain Current@T _A (V _{GS} =10V) ^③	T _A =25°C	28	
		T _A =70°C	21	
P _D	Maximum Power Dissipation@T _C	T _C =25°C	54	W
		T _C =100°C	22	
	Maximum Power Dissipation@T _A ^③	T _A =25°C	4.2	
		T _A =70°C	2.7	

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	2.3	$^{\circ}\text{C/W}$
$R_{\theta JA}^{(3)}$	Thermal Resistance-Junction to Ambient	30	$^{\circ}\text{C/W}$
Drain-Source Avalanche Ratings			
$E_{AS}^{(4)}$	Avalanche Energy, Single Pulsed	156	mJ

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU3091M			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V			1	μA
		T _J =125°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1		2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^⑤	Drain-Source On-state Resistance	V _{GS} =4.5V, I _{DS} =35A		3.4	4.5	mΩ
		V _{GS} =10V, I _{DS} =50A		2.8	3.5	mΩ
Diode Characteristics						
V _{SD} ^⑤	Diode Forward Voltage	I _{SD} =50A, V _{GS} =0V			1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =50A, dI _{SD} /dt=100A/μs		30		ns
Q _{rr}	Reverse Recovery Charge			36		nC
Dynamic Characteristics ^⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		1.3		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz		3280		pF
C _{oss}	Output Capacitance			580		
C _{rss}	Reverse Transfer Capacitance			290		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, I _{DS} =20A, V _{GEN} =10V, R _G =4.7Ω		8		ns
t _r	Turn-on Rise Time			12		
t _{d(OFF)}	Turn-off Delay Time			35		
t _f	Turn-off Fall Time			9		
Gate Charge Characteristics ^⑥						
Q _g	Total Gate Charge	V _{DS} =24V, V _{GS} =10V, I _{DS} =20A		60		nC
Q _{gs}	Gate-Source Charge			15		
Q _{gd}	Gate-Drain Charge			22		

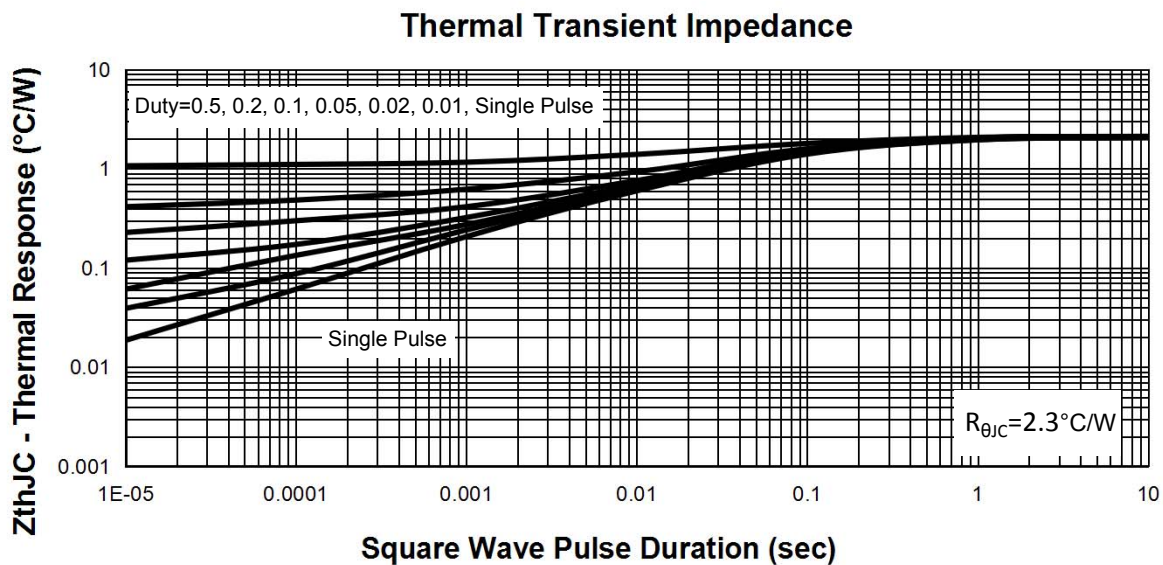
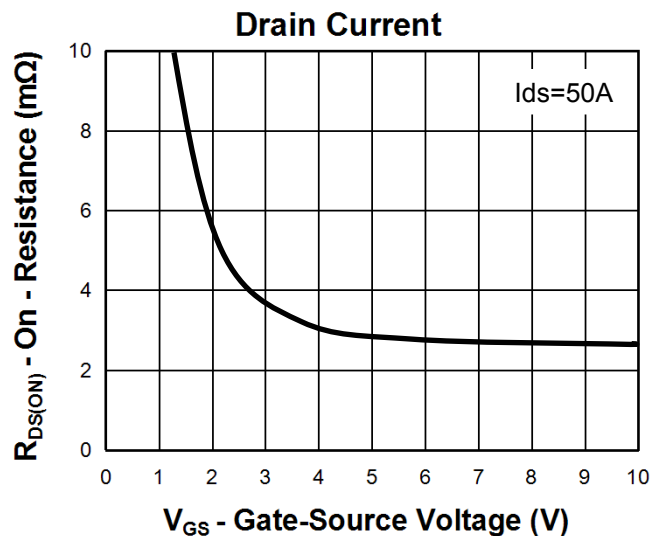
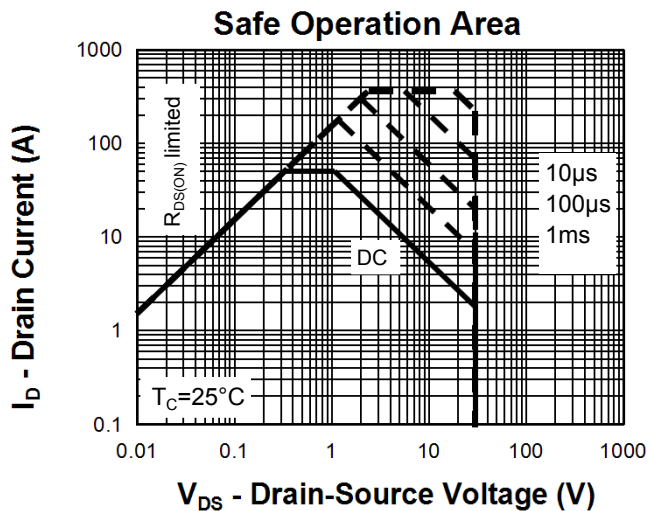
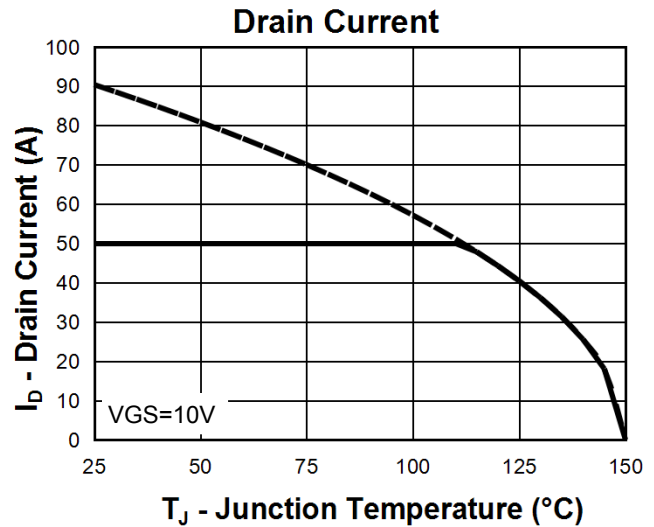
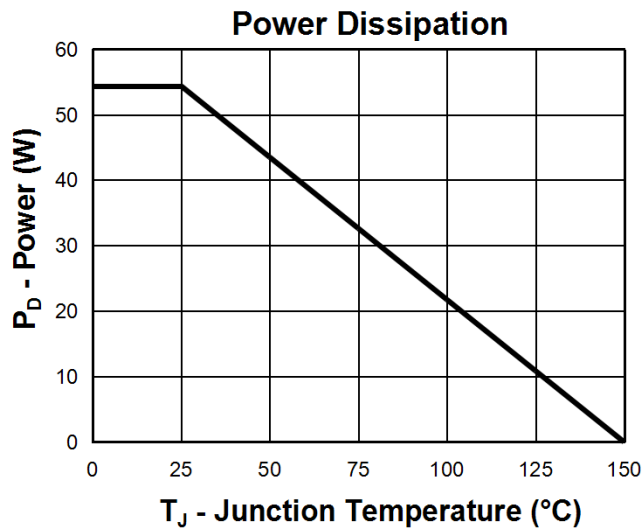
Notes:

- ① Max current is limited to 50A by the package.
- ② Pulse width limited by safe operating area.
- ③ When mounted on 1 inch square copper board, t 10sec.
- ④ Limited by TJmax, IAS =25A, VDD =24V, RG = 50Ω , Starting TJ = 25° C.
- ⑤ Pulse test ; Pulse width300s, duty cycle2%.
- ⑥ Guaranteed by design, not subject to production testing.

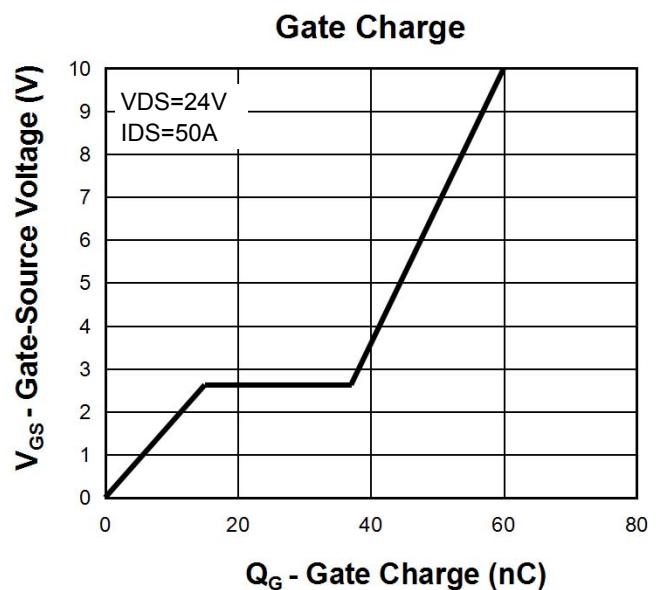
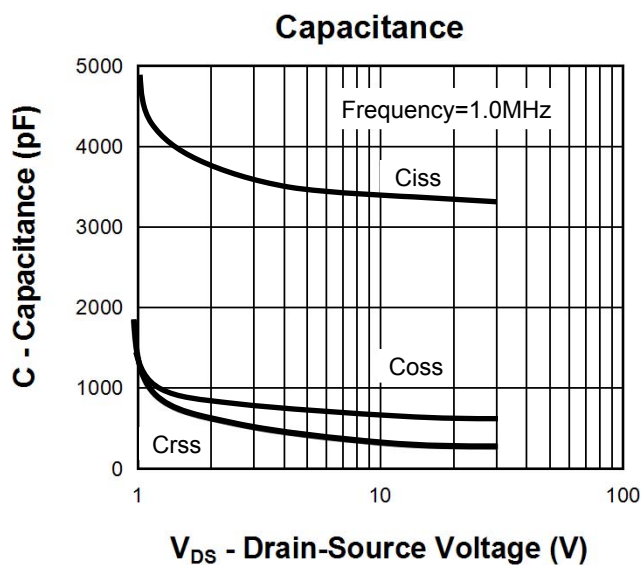
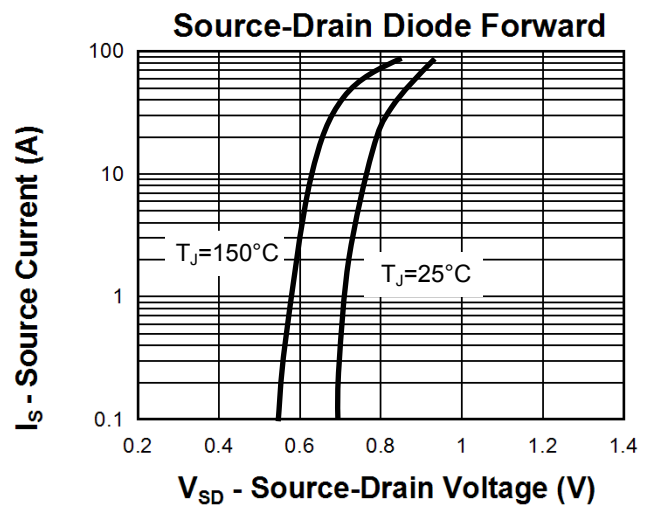
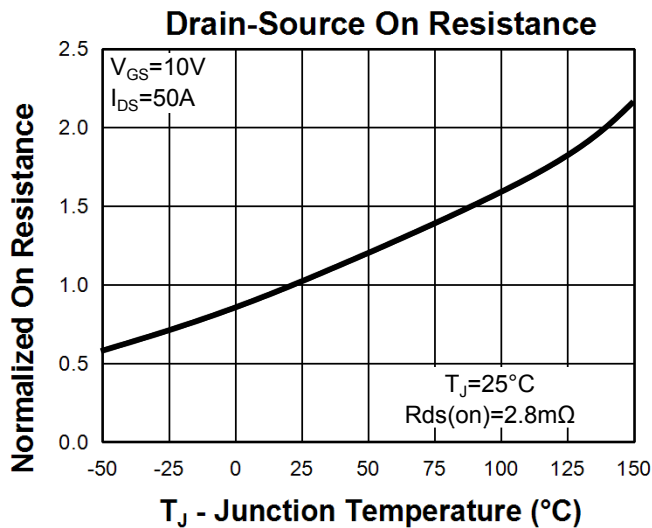
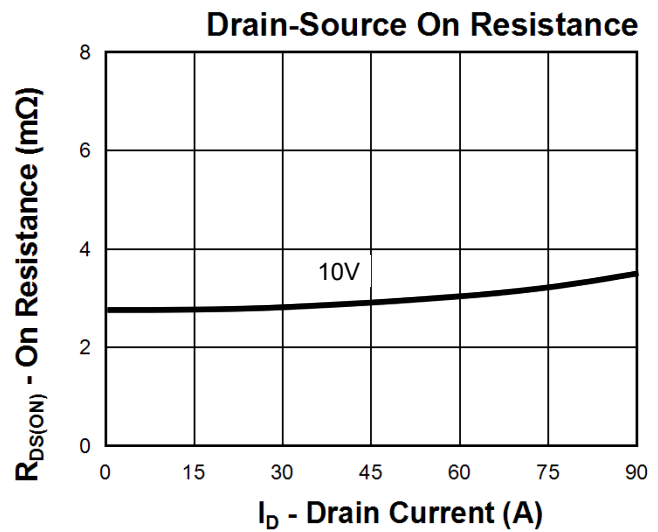
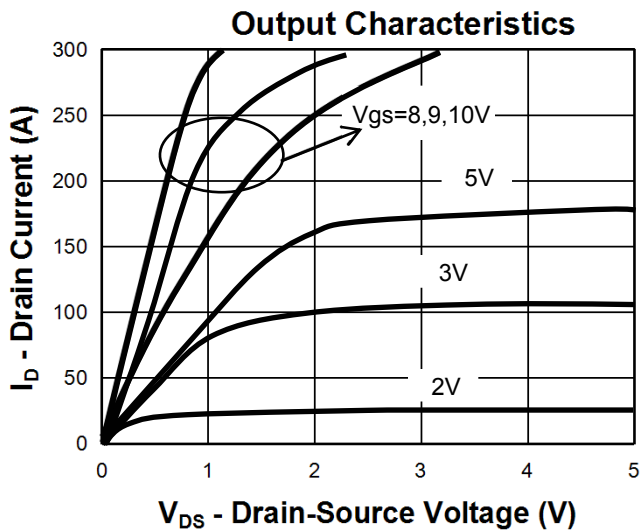
Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU3091M	RU3091M	PDFN5060	Tape&Reel	3000	13"	12mm

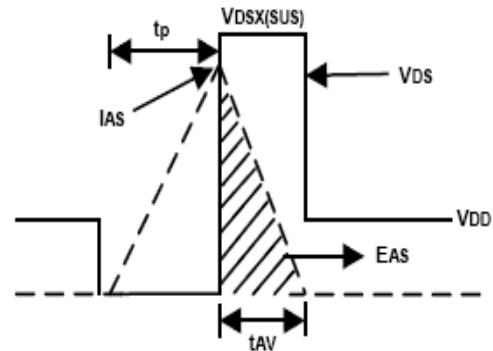
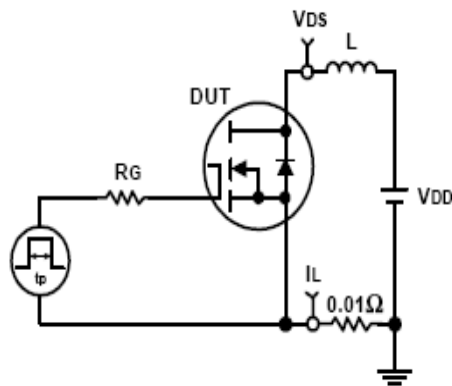
Typical Characteristics



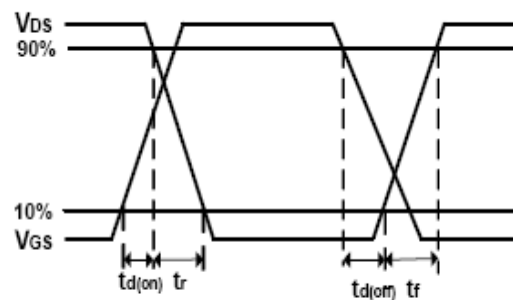
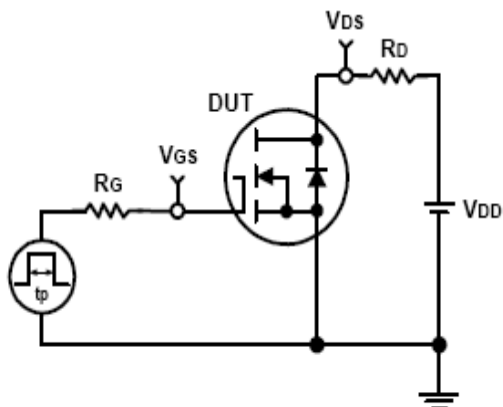
Typical Characteristics



Avalanche Test Circuit and Waveforms

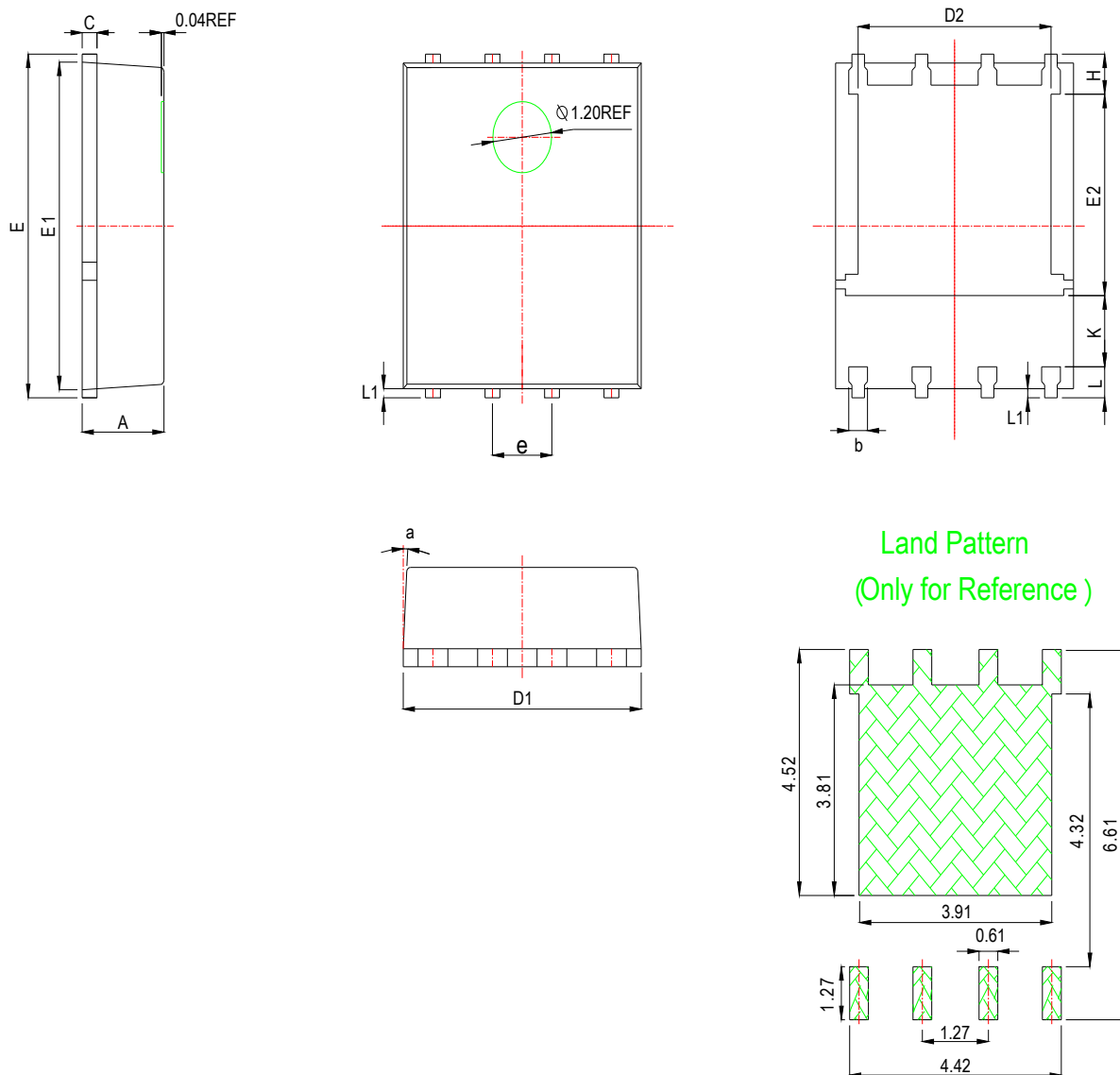


Switching Time Test Circuit and Waveforms



Package Information

PDFN5060



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
b	0.33	0.42	0.51	0.013	0.017	0.020
c	0.20	0.25	0.30	0.008	0.010	0.012
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.61	3.79	3.96	0.142	0.149	0.156
E	5.90	6.00	6.10	0.232	0.236	0.240
E1	5.65	5.75	5.85	0.222	0.226	0.230
E2	3.38	3.58	3.78	0.133	0.141	0.149
e	1.27 BSC			0.005 BSC		
H	0.41	0.51	0.61	0.016	0.020	0.024
k	1.10			0.043		
L	0.51	0.61	0.71	0.020	0.024	0.028
L1	0.06	0.13	0.20	0.002	0.005	0.008
a	0°		12°	0°		12°

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